TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP281,TLP281-4

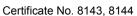
PROGRAMMABLE CONTROLLERS AC/DC-INPUT MODULE PC CARD MODEM(PCMCIA)

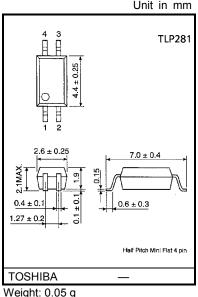
TLP281 and TLP281-4 is a very small and thin coupler, suitable for surface mount assembly in applications such as PCMCIA Fax modem, programmable controllers.

TLP281 and TLP281-4 consist of photo transistor, optically coupled to a gallium arsenide infrared emitting diode.

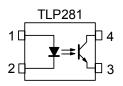
- Collector-Emitter Voltage : 80 V (MIN)
- Current Transfer Ratio : 50% (MIN) • Rank GB
- Isolation Voltage
- **UL Recognized**
- **BSI** Approved

: 100% (MIN) : 2500 Vrms (MIN) : UL1577 , File No. E67349 : BS EN 60065: 1994, : BS EN 41003: 1997

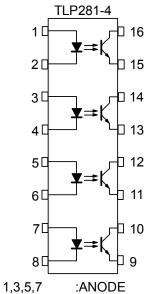




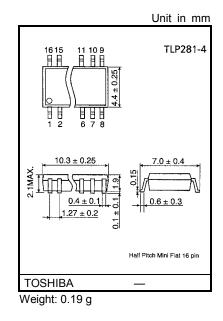
PIN CONFIGURATION(Top view)



1:ANODE 2:CATHODE **3:EMITTER** 4:COLLECTOR



:CATHODE 2.4.6.8 9,11,13,15 :EMITTER 10,12,14,16 :COLLECTOR



Unit in mm

TYPE	Classi- Fication(*1)	Current Transfer Ration (%) (I_C / I_F) I_F = 5 mA, V_{CE} = 5 V, Ta = 25°CMinMax		Marking of Classification		
	Blank	50	600	Blank ,Y [■] ,YE,G,G [■] ,GR,B,BL,GB		
	Rank Y	50	150	YE		
	Rank GR	100	300	GR		
	Rank BL	200	600	BL		
TLP281	Rank GB	100	600	GB		
	Rank YH	75	150	Y		
	Rank GRL	100	200	G		
	Rank GRH	150	300	G		
	Rank BLL	200	400	В		
TLP281-4	Blank	50	600	Blank , GB		
1LF201-4	Rank GB	100	600	GB		

*1: Ex. rank GB: TLP281 (GB)

(Note): Application type name for certification test, please use standard product type name, i.e. TLP281 (GB): TLP281–1 , TLP281–4 (GB): TLP281–4

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RAT	UNIT		
	CHARACTERISTIC	SYMBOL	TLP281	TLP281-4	UNIT	
Forward Current		١ _F	50		mA	
Î	Forward Current Derating	∆I _F /°C	−0.7 (Ta≥53°C)	−0.5 (Ta≥25°C)	mA /°C	
LED	Pulse Forward Current	I _{FP}	1		А	
Reverse Voltage	Reverse Voltage	V _R	5		V	
	Junction Temperature	Тј	12	°C		
	Collector-Emitter Voltage	V _{CEO}	8	80		
	Emitter-Collector Voltage	V _{ECO}	7		V	
OR	Collector Current	Ι _C	50		mA	
DETE	Collector Power Dissipation (1 Circuit)	P _C	150	100	mW	
	Collector Power Dissipation Derating(Ta≥25°C) (1 Circuit)	∆P _C /°C	-1.5	-1.0	mW /°C	
	Junction Temperature	Тј	12	25	°C	
Оре	erating Temperature Range	T _{opr}	-55-	°C		
Storage Temperature Range		T _{stg}	-55~125		°C	
Lead Soldering Temperature		T _{sol}	260 (10s)		°C	
Total Package Power Dissipation (1 Circuit)		PT	200	170	mW	
Total Package Power Dissipation Derating (Ta≥25°C) (1 Circuit)		∆P _T /°C	-2.0	-1.7	mW /°C	
Isola	ation Voltage (Note1)	BVS	2500(AC,1mi	n,R.H.≤60%)	Vrms	

(Note1)Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
	Forward Voltage	VF	I _F = 10 mA	1.0	1.15	1.3	V
LED	Reverse Current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	CT	V = 0, f = 1 MHz	_	30	_	pF
	Collector-Emitter Breakdown Voltage	V _(BR) CEO	I _C = 0.5 mA	80	_	_	v
OR	Emitter-Collector Breakdown Voltage	V _{(BR) ECO}	I _E = 0.1 mA	7	_	_	V
DETECTOR	Collector Dark Current	ICEO	V _{CE} = 48 V, Ambient Light Below (100 tx)		0.01 (2)	0.1 (10)	μA
	(Note2)		V _{CE} = 48 V, Ta = 85°C Ambient Light Below (100 tx)		2 (4)	50 (50)	μA
	Capacitance (Collector to Emitter)	C _{CE}	V = 0, f = 1 MHz	_	10	_	pF

(Note 2) Because of the construction, leak current might be increased by ambient light.

Please use photocoupler with less ambient light.

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I _C / I _F	I _F = 5 mA, V _{CE} = 5 V	50	_	600	%
		Rank GB	100	_	600	
Saturated CTR	I _C / I _{F (sat)}	IF = 1 mA, VCE = 0.4 V	-	60	_	%
Saturated CTR		Rank GB	30	_	_	70
Collector-Emitter		I _C = 2.4 mA, I _F = 8 mA	_	_	0.4	
Saturation Voltage	V _{CE (sat)}	I _C = 0.2 mA, I _F = 1 mA	_	0.2	_	V
Saturation voltage		Rank GB	_	_	0.4	
Off-State Collector Current	I _{C (off)}	V _F = 0.7 V, V _{CE} = 48 V	_	_	10	μA

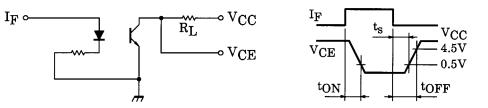
ISOLATION CHARACTERISTICS (Ta = 25°C)

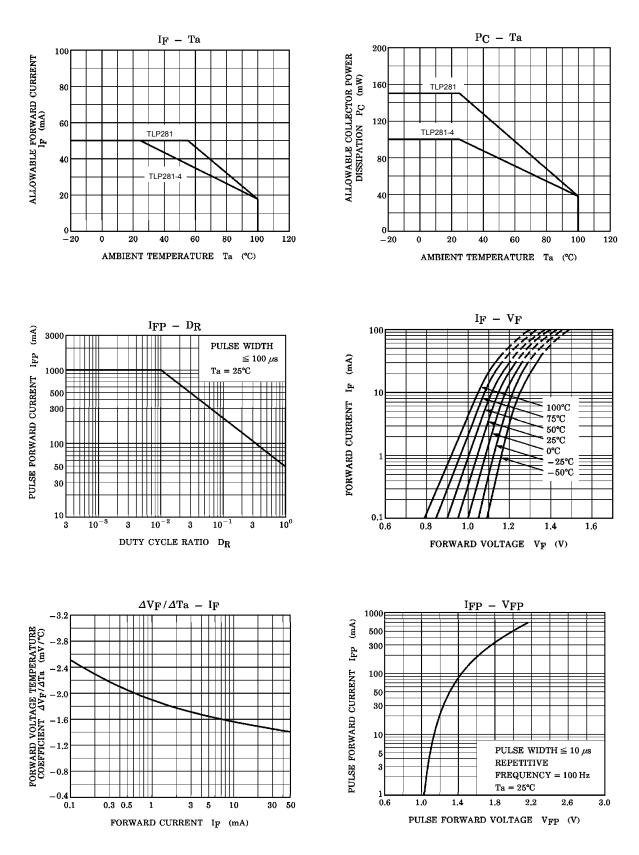
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	CS	V _S = 0 V, f = 1 MHz	_	0.8	_	pF
Isolation Resistance	R _S	V _S = 500 V, R.H.≤60%	5×10 ¹⁰	10 ¹⁴	_	Ω
		AC, 1 minute	2500	_	_	Vrms
Isolation Voltage	BVS	AC , 1 second,in OIL		5000	_	VIIIIS
		DC , 1 minute, in OIL	_	5000	—	Vdc

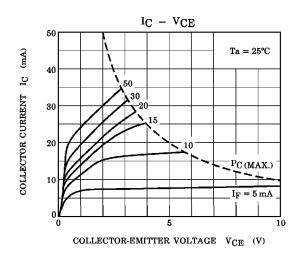
SWITCHING CHARACTERISTICS (Ta = 25°C)

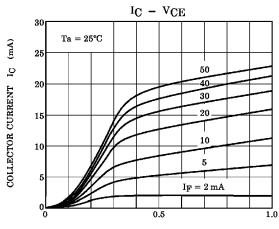
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	tr		_	2	—	
Fall Time	t _f	V _{CC} = 10 V, I _C = 2 mA	_	3	_	μs
Turn-On Time	t _{on}	R _L = 100Ω	_	3	—	μο
Turn-Off Time	t _{off}		_	3	_	
Turn-On Time	t _{ON}	R _L = 1.9 kΩ (Fig.1) V _{CC} = 5 V, I _F = 16 mA	_	2	—	
Storage Time	ts		_	25	—	μs
Turn-Off Time	t _{OFF}		_	40	_	

(Fig.1)SWITCHING TIME TEST CIRCUIT

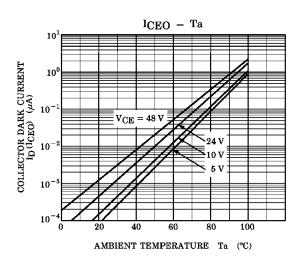


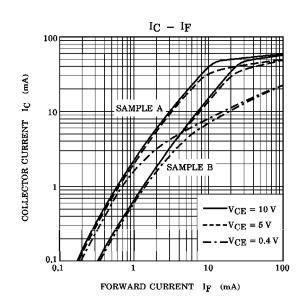


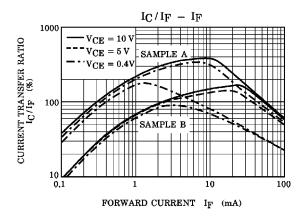


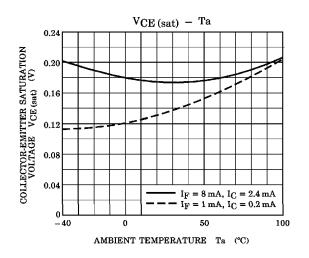


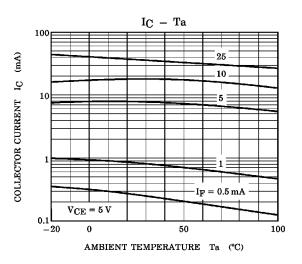
Collector-emitter voltage V_{CE} (V)

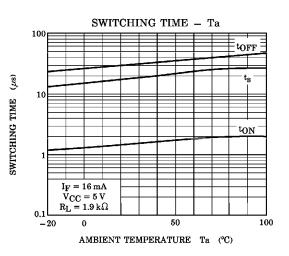


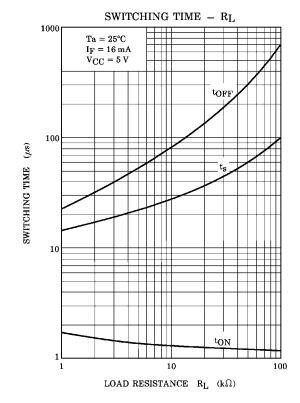












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